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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q80553

Toshiro HAYAKAWA

Appln. No.: 10/804,216

Group Art Unit: 2828

Confirmation No.: 6095

Examiner: Dung T. NGUYEN

Filed: March 19, 2004

For: SURFACE-EMITTING SEMICONDUCTOR LASER ELEMENT HAVING
SELECTIVE-OXIDATION TYPE OR ION-INJECTION TYPE CURRENT-
CONFINEMENT STRUCTURE, InGaAsP QUANTUM WELL, AND InGaP OR
InGaAsP BARRIER LAYERS

PETITION FOR EXTENSION OF TIME UNDER 37 C.F.R. § 1.136

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. § 1.136, Applicant hereby petitions for an extension of time of one
(1) month, extending the time for responding to the Office Action of August 1, 2006 to
December 1, 2006.

A check for the statutory fee of \$120.00 is attached. The USPTO is directed and
authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to
Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account. A
duplicate copy of this sheet is enclosed.

Respectfully submitted,

SUGHRUE MION, PLLC
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12/04/2006 HMARZ11 00000085 10004216
Abraham J. Rosen
Registration No. 33,276 120.00 OP

WASHINGTON OFFICE
23373
CUSTOMER NUMBER

Date: December 1, 2006